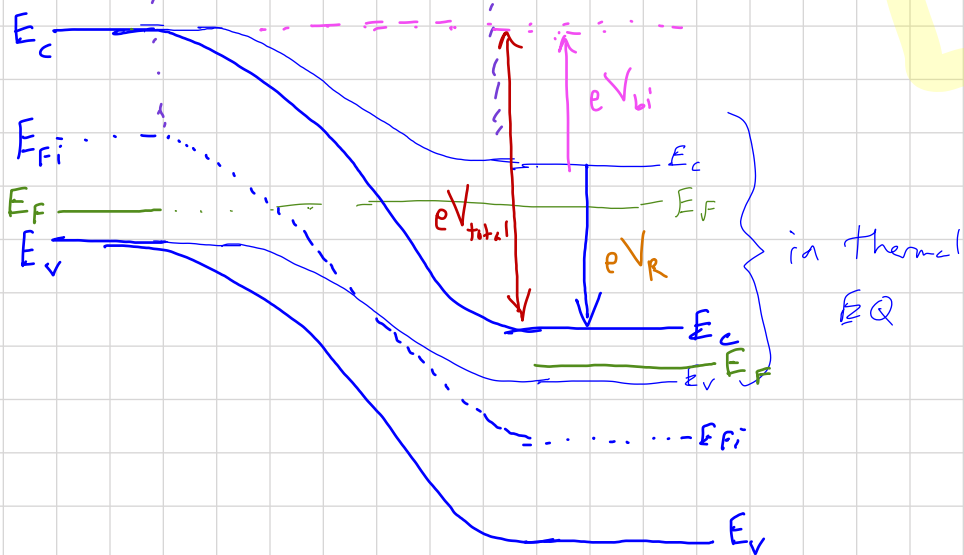
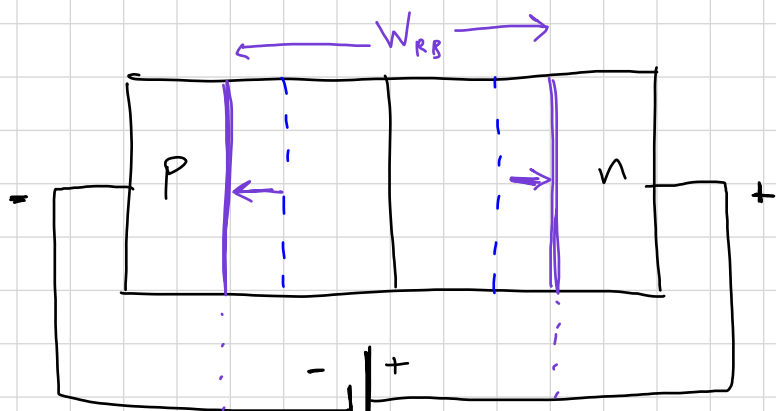


Lecture # 9

pn Junctions under bias

Applying a Reverse Bias



$$V_{total} = |\phi_{Fn}| + |\phi_{Fp}| + V_R$$

$$V_{Total} = V_{bi} + V_R$$

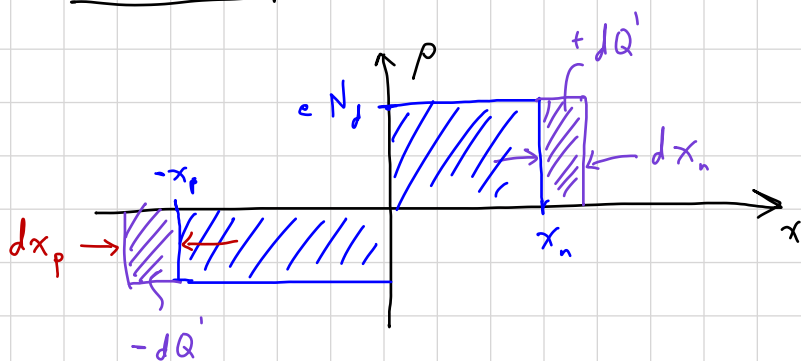
Depletion width has grown under V_R :

$$W_{RB} = \left[\frac{2\epsilon_s\epsilon_0}{e} \left(\frac{N_a + N_d}{N_a N_d} \right) (V_{bi} + V_R) \right]^{1/2}$$

Max E-field still occurs at metallurgical junction:

$$\epsilon_{max} = \frac{-2(V_{bi} + V_R)}{W_{RB}}$$

Junction Capacitance



expansion of W with change in V_R (dV_R) yields a junction capacitance:

$$C' = \frac{dQ'}{dV_R} \left(F/cm^2 \right), \quad F = \frac{C}{V}$$

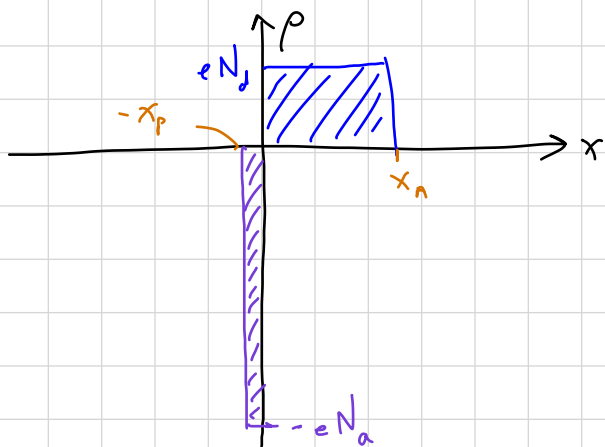
where:

$$dQ' = eN_d dx_n = eN_a dx_p$$

$$\therefore C' = \left[\frac{e\epsilon_s\epsilon_0 N_a N_d}{2(V_{bi} + V_R)(N_a + N_d)} \right]^{1/2}$$

one-sided junctions

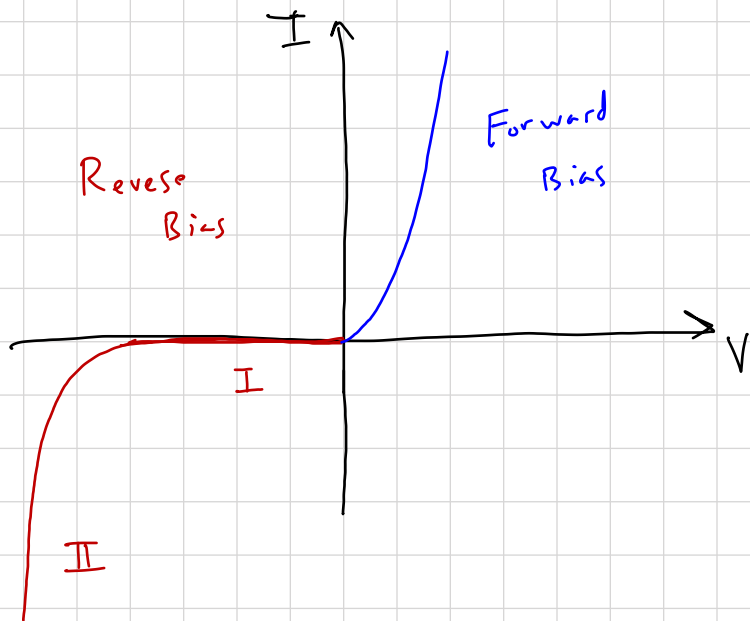
Example: p^+n heavy p-doping



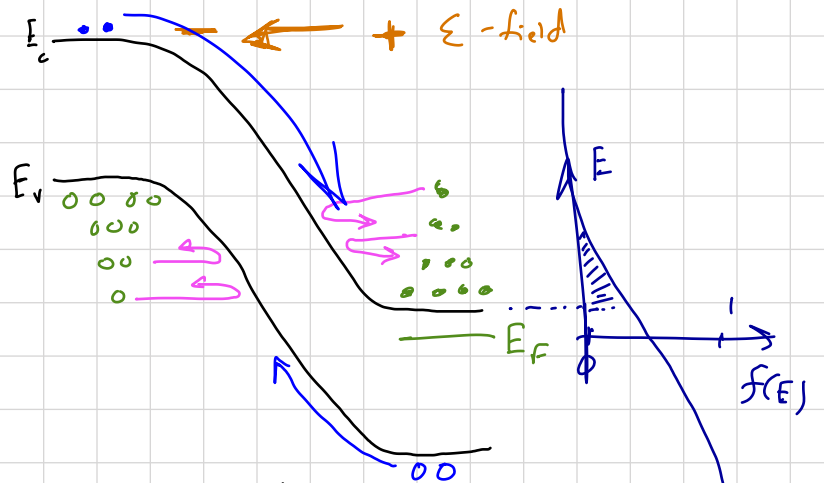
Can use this to approx. W since it will be $\sim x_n$:

$$W_{RB} \approx \left[\frac{2\epsilon_s\epsilon_0(V_{bi} + V_R)}{eN_d} \right]^{1/2}$$

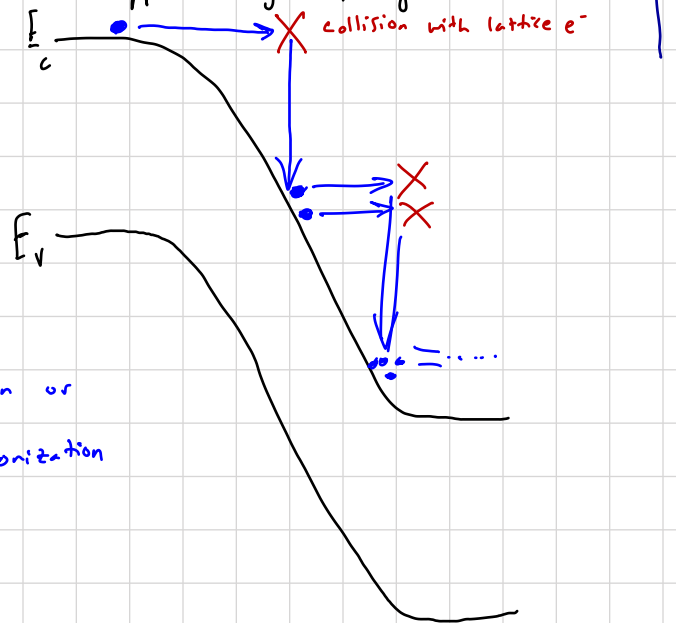
Junction Breakdown



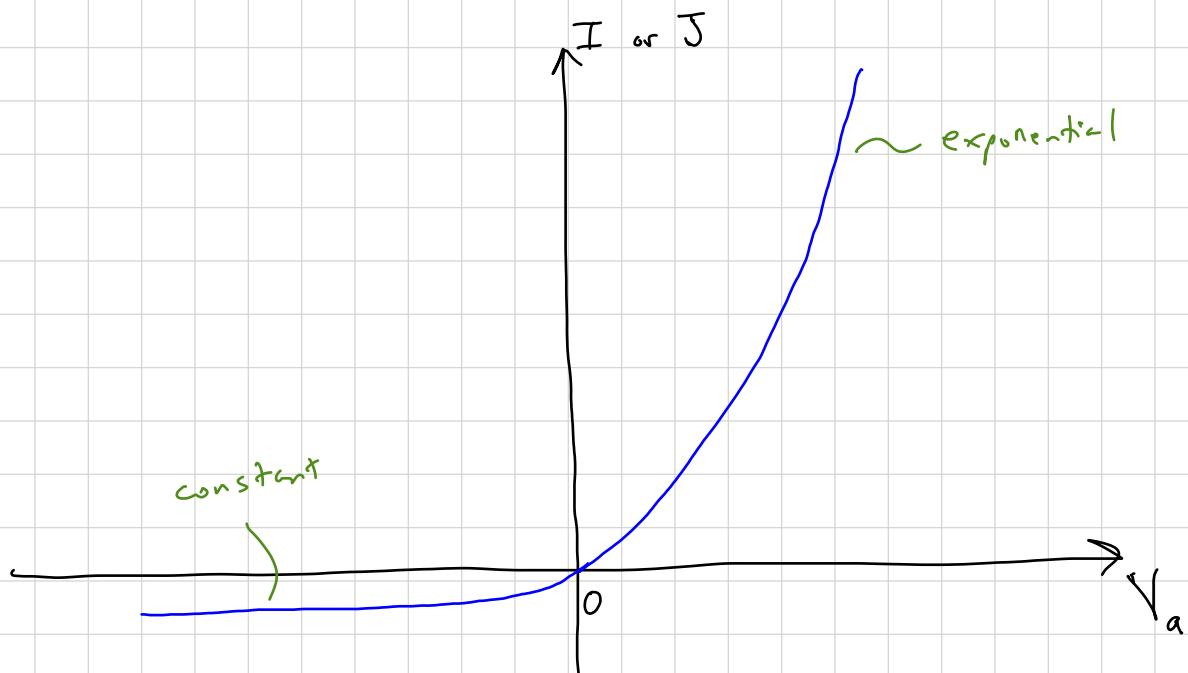
Region (I): No current (very small) from minority carriers



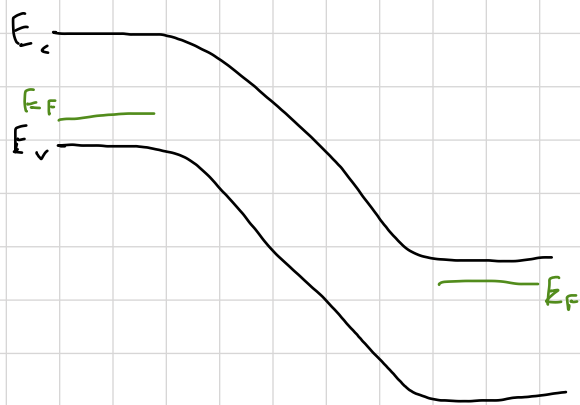
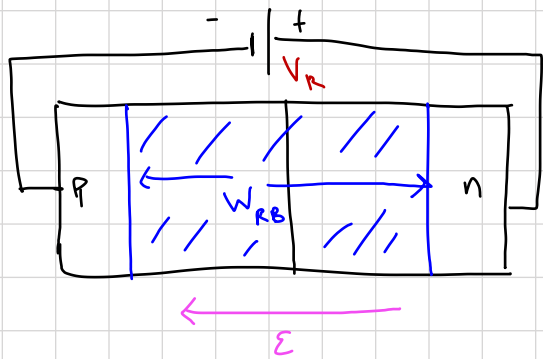
Region (II) Breakdown, e^- collide with lattice e^- s, creating an $e^- h^+$ pair; this happens again & again



"Avalanche"
Breakdown or
Impact Ionization

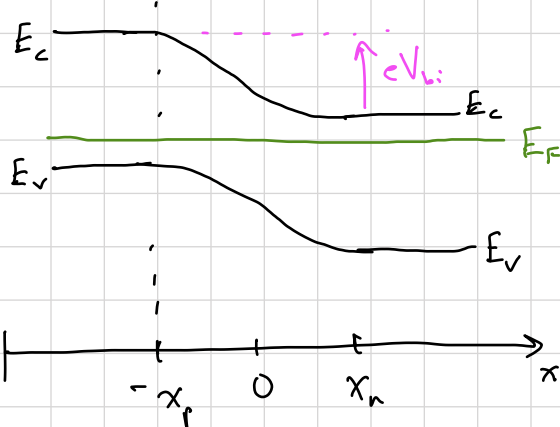
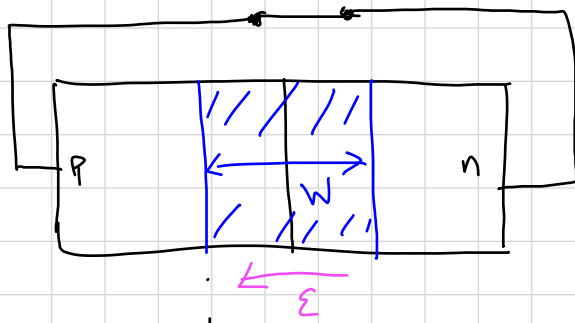


Reverse-bias ($-V_a$)



(previous page)

Zero-bias (thermal EQ)



$$p_{p0} = N_a$$

$$n_{n0} = N_d$$

$p_p \rightarrow$ majority carrier h^+ in p-region

$n_n \rightarrow$ majority carrier e^- in n-region

$p_n \rightarrow$ minority carrier h^+ in n-region

$n_p \rightarrow$ minority carrier e^- in p-region

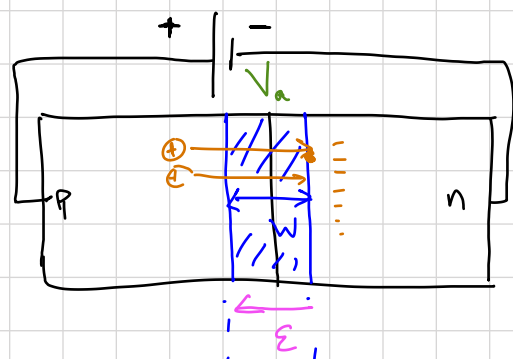
$$n_{p0} = \frac{n_i^2}{N_a}$$

$$p_{n0} = \frac{n_i^2}{N_d}$$

$$V_{bi} = V_t \ln \left(\frac{N_a N_d}{n_i^2} \right)$$

$$n_{p0} = n_{n0} \exp \left(\frac{-eV_{bi}}{kT} \right)$$

Forward-bias ($+V_a$)



$$n_p = n_{p0} \exp \left(\frac{eV_a}{kT} \right)$$

(used at $-x_p$)

$$p_n = p_{n0} \exp \left(\frac{eV_a}{kT} \right)$$

(used at x_n)

Excess minority carrier concentrations:

$$\delta n_p(x) = n_p(x) - n_{p0} = n_{p0} \left[\exp \left(\frac{eV_a}{kT} \right) - 1 \right] \exp \left(\frac{x_p + x}{L_n} \right)$$

mean free distance a minority carrier travels before recombining

$$\delta p_n(x) = p_n(x) - p_{n0} = p_{n0} \left[\exp \left(\frac{eV_a}{kT} \right) - 1 \right] \exp \left(\frac{x_n - x}{L_p} \right)$$

$L = \sqrt{D\tau}$

$$E_{Fn} = E_{Fi} + kT \ln \left(\frac{n}{n_i} \right)$$

$$E_{Fp} = E_{Fi} - kT \ln \left(\frac{p}{n_i} \right)$$

$$n_p p_n = n_p = n_i^2 \exp \left(\frac{E_{Fn} - E_{Fp}}{kT} \right)$$